

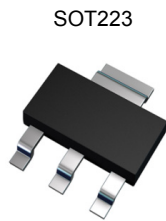
## Product Summary

- Continuous Drain Source Voltage 60V
- On-State Resistance 100mΩ
- Nominal Load Current ( $V_{IN} = 5V$ ) 2.8A
- Clamping Energy 480mJ

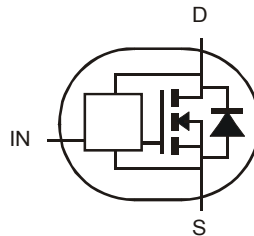
## Description and Applications

The ZXMS6006SGQ is a self protected low side MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6006SGQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

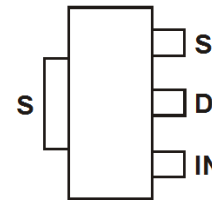
- Lamp Driver
- Motor Driver
- Relay Driver
- Solenoid Driver



Top View



Device Symbol



Top View  
Pin Out

## Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (active clamp)
- Thermal Shutdown with Auto Restart
- Over-Current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- **Lead-Free Finish; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable**

## Mechanical Data

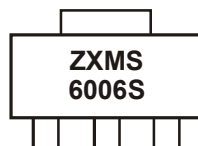
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (approximate)

## Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6006SGQTA	ZXMS6006S	7	12	1,000

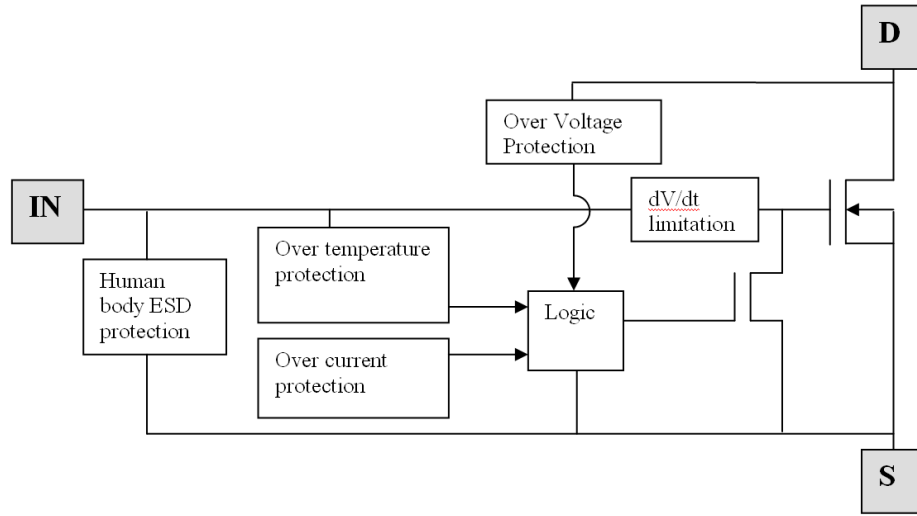
- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



ZXMS6006S = Product type Marking Code

**Functional Block Diagram**



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V
Drain-Source Voltage for Short Circuit Protection	V <sub>DS(SC)</sub>	16	V
Continuous Input Voltage	V <sub>IN</sub>	-0.5 to +6.0	V
Continuous Input Current @-0.2V ≤ V <sub>IN</sub> ≤ 6V	I <sub>IN</sub>	No Limit	mA
Continuous Input Current @V <sub>IN</sub> < -0.2V or V <sub>IN</sub> > 6V	I <sub>IN</sub>	I <sub>IN</sub>   ≤ 2	mA
Pulsed Drain Current @V <sub>IN</sub> = 3.3V	I <sub>DM</sub>	11	A
Pulsed Drain Current @V <sub>IN</sub> = 5V	I <sub>DM</sub>	13	A
Continuous Source Current (Body Diode) (Note 5)	I <sub>S</sub>	2	A
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	12	A
Unclamped Single Pulse Inductive Energy, T <sub>J</sub> = +25°C, I <sub>D</sub> = 0.5A, V <sub>DD</sub> = 24V	E <sub>AS</sub>	480	mJ
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4000	V
Charged Device Model	V <sub>CDM</sub>	1000	V

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Power Dissipation at T <sub>A</sub> = +25°C (Note 5)	P <sub>D</sub>	1.0	W
Linear Derating Factor	P <sub>D</sub>	8.0	mW/°C
Power Dissipation at T <sub>A</sub> = +25°C (Note 6)	P <sub>D</sub>	1.6	W
Linear Derating Factor	P <sub>D</sub>	12.8	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	125	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	39	°C/W
Operating Temperature Range	T <sub>J</sub>	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

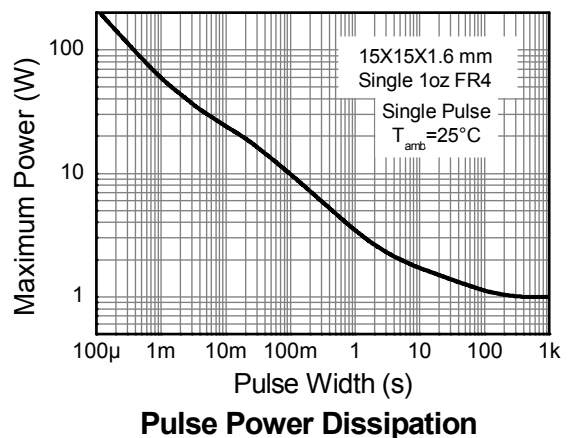
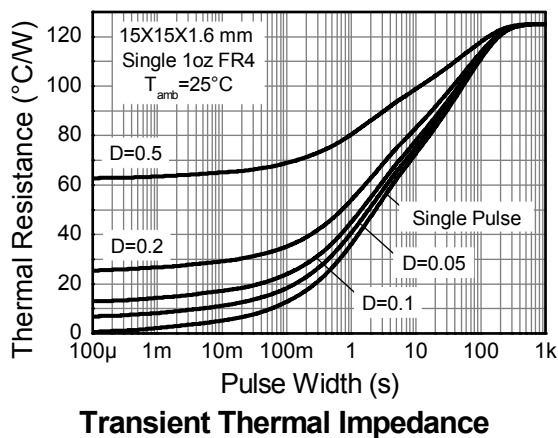
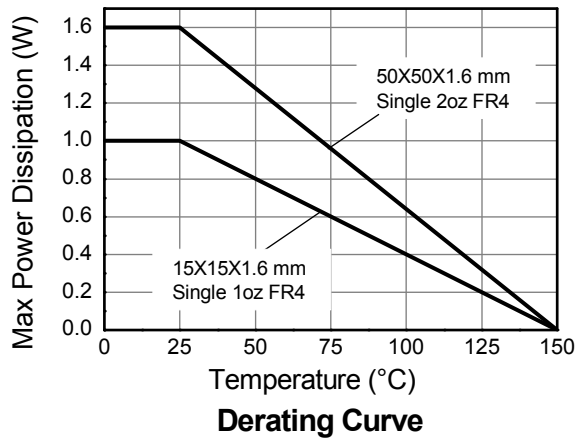
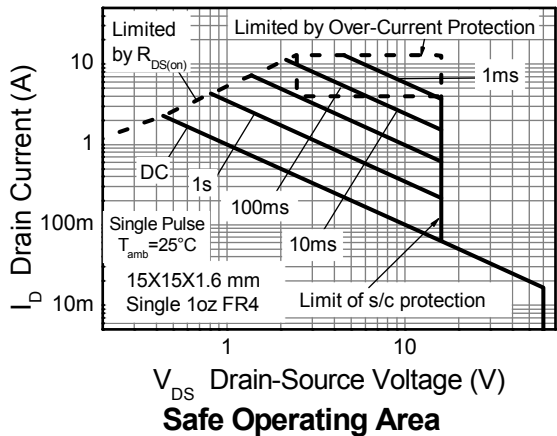
- Notes:
- For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.
  - For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.
  - Thermal resistance between junction and the mounting surfaces of drain and source pins.

**Recommended Operating Conditions**

The ZXMS6006SGQ is optimized for use with  $\mu\text{C}$  operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	$V_{IN}$	0	5.5	V
Ambient Temperature Range	$T_A$	-40	+125	$^{\circ}\text{C}$
High Level Input Voltage for MOSFET to be on	$V_{IH}$	3	5.5	V
Low Level Input Voltage for MOSFET to be off	$V_{IL}$	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	$V_P$	0	16	V

**Thermal Characteristics**

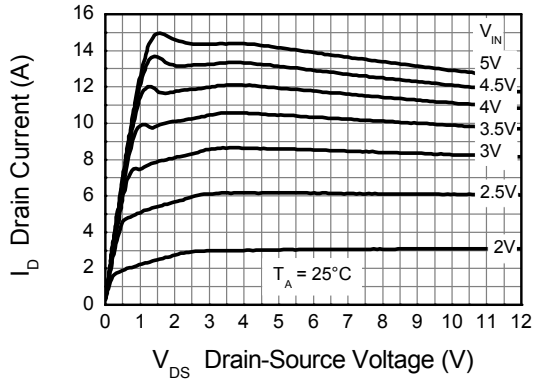


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

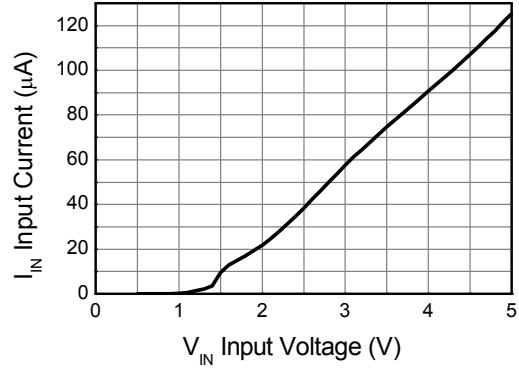
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>Static Characteristics</b>						
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	65	70	V	I <sub>D</sub> = 10mA
Off State Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V
		—	—	2		V <sub>DS</sub> = 36V, V <sub>IN</sub> = 0V
Input Threshold Voltage	V <sub>IN(th)</sub>	0.7	1	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Input Current	I <sub>IN</sub>	—	60	100	μA	V <sub>IN</sub> = +3V
		—	120	400		V <sub>IN</sub> = +5V
Input Current While Over Temperature Active	—	—	—	300	μA	V <sub>IN</sub> = +5V
Static Drain-Source On-State Resistance	R <sub>DS(on)</sub>	—	85	125	mΩ	V <sub>IN</sub> = +3V, I <sub>D</sub> = 1A
		—	75	100		V <sub>IN</sub> = +5V, I <sub>D</sub> = 1A
Continuous Drain Current (Note 5)	I <sub>D</sub>	2.0	—	—	A	V <sub>IN</sub> = 3V; T <sub>A</sub> = +25°C
Continuous Drain Current (Note 6)		2.2	—	—		V <sub>IN</sub> = 5V; T <sub>A</sub> = +25°C
		2.6	—	—		V <sub>IN</sub> = 3V; T <sub>A</sub> = +25°C
		2.8	—	—		V <sub>IN</sub> = 5V; T <sub>A</sub> = +25°C
Current Limit (Note 8)	I <sub>D(LIM)</sub>	4	8	—	A	V <sub>IN</sub> = +3V
		6	13	—		V <sub>IN</sub> = +5V
<b>Dynamic Characteristics</b>						
Turn On Delay Time	t <sub>d(on)</sub>	—	8.6	—	μs	V <sub>DD</sub> = 12V, I <sub>D</sub> = 1A, V <sub>GS</sub> = 5V
Rise Time	t <sub>r</sub>	—	18	—		
Turn Off Delay Time	t <sub>d(off)</sub>	—	34	—		
Fall Time	t <sub>f</sub>	—	15	—		
<b>Over-Temperature Protection</b>						
Thermal Overload Trip Temperature (Note 9)	T <sub>JT</sub>	150	175	—	°C	—
Thermal Hysteresis (Note 9)	f <sub>f</sub>	—	10	—	°C	—

- Notes:
8. The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
  9. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods..

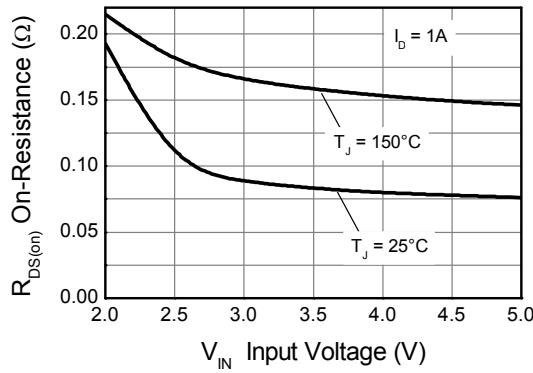
**Typical Characteristics**



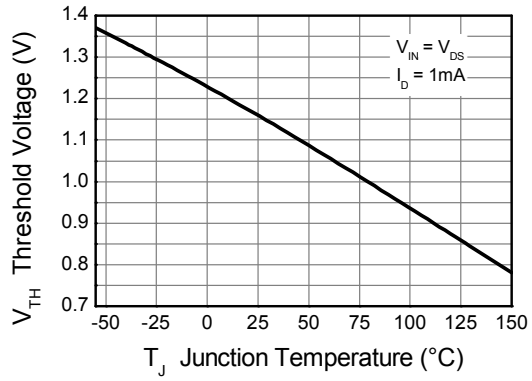
**Typical Output Characteristic**



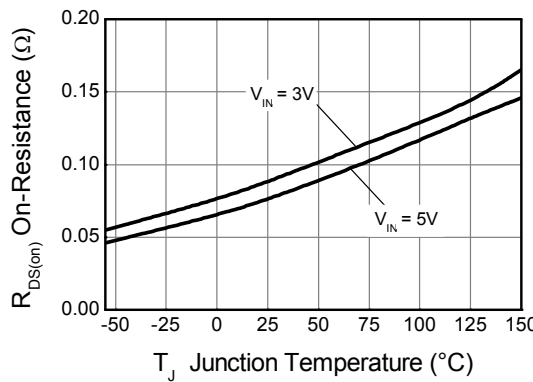
**Input Current vs Input Voltage**



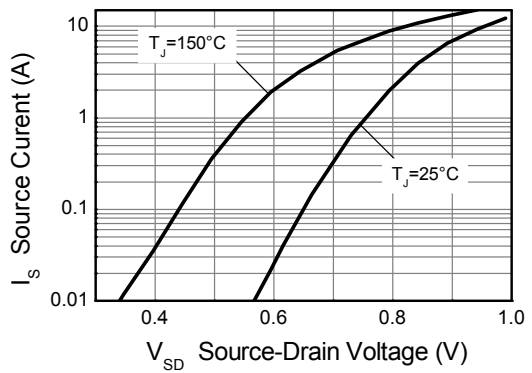
**On-Resistance vs Input Voltage**



**Threshold Voltage vs Temperature**

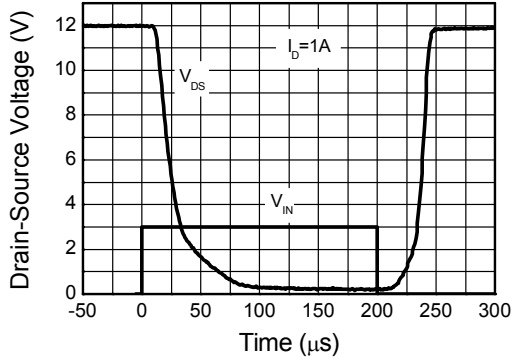


**On-Resistance vs Temperature**

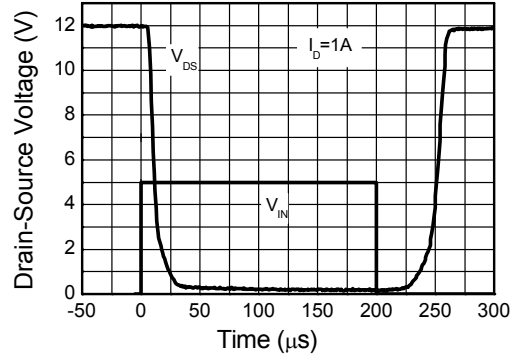


**Reverse Diode Characteristic**

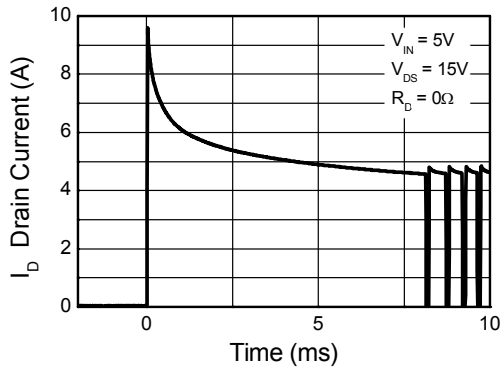
**Typical Characteristics (cont.)**



**Switching Speed**



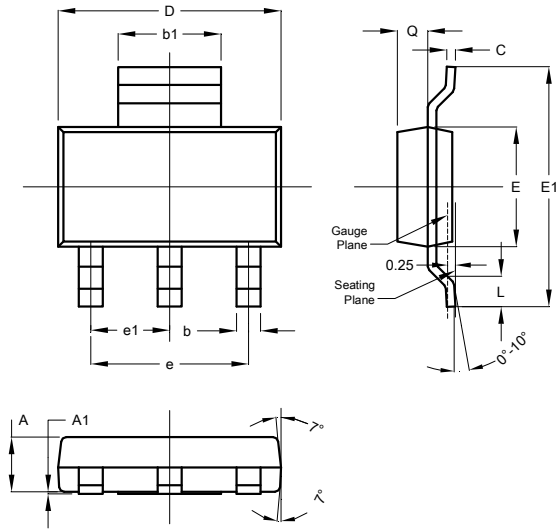
**Switching Speed**



**Typical Short Circuit Protection**

**Package Outline Dimensions**

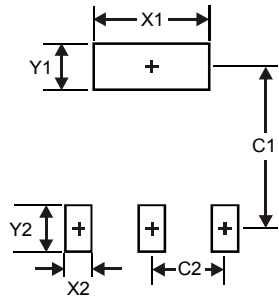
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

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